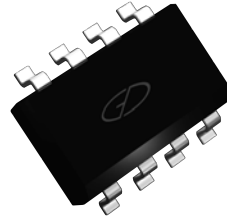
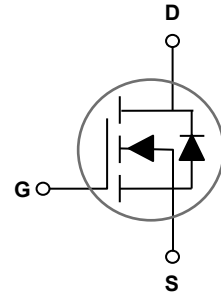


Main Product Characteristics

$V_{(BR)DSS}$	100V
$R_{DS(ON)}$	9.2m Ω
I_D	12A



SOP-8



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for networking, load switch, quick charger and LED applications
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The SSF0976 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	+20 / -12	V
Drain Current – Continuous (T _C =25°C) (Chip Limitation)	I_D	12	A
Drain Current – Continuous (T _C =100°C) (Chip Limitation)		7.6	A
Drain Current – Pulsed ¹	I_{DM}	48	A
Single Pulse Avalanche Energy ²	E_{AS}	211	mJ
Single Pulse Avalanche Current ²	I_{AS}	65	A
Power Dissipation (T _C =25°C)	P_D	5	W
Power Dissipation – Derate above 25°C		0.04	W/°C
Storage Temperature Range Operating	T_{STG}	-50 to +150	°C
Junction Temperature Range	T_J	-50 to +150	°C

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	---	62	°C/W
Thermal Resistance Junction to Case	$R_{\theta JC}$	---	25	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=1\text{mA}$	---	0.054	---	$V/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=80V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=+20V, V_{DS}=0V$	---	---	100	μA
On Characteristics						
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=8.5A$	---	7.6	9.2	$m\Omega$
		$V_{GS}=4.5V, I_D=4A$	---	10.8	14	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	-5.5	---	$mV/^\circ\text{C}$
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=3A$	---	11	---	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3, 4}	Q_g	$V_{DS}=80V, V_{GS}=10V, I_D=8.5A$	---	39.7	80	nC
Gate-Source Charge ^{3, 4}	Q_{gs}		---	5.4	10	
Gate-Drain Charge ^{3, 4}	Q_{gd}		---	11.2	22	
Turn-On Delay Time ^{3, 4}	$T_{d(on)}$	$V_{DD}=50V, V_{GS}=10V, R_G=6\Omega, I_D=1A$	---	14.6	30	nS
Rise Time ^{3, 4}	T_r		---	21.5	44	
Turn-Off Delay Time ^{3, 4}	$T_{d(off)}$		---	54	108	
Fall Time ^{3, 4}	T_f		---	84.3	168	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	---	2550	5100	pF
Output Capacitance	C_{oss}		---	685	1370	
Reverse Transfer Capacitance	C_{rss}		---	42	84	
Gate Resistance	R_g	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	1.43	---	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V, \text{Force Current}$	---	---	12	A
Pulsed Source Current	I_{SM}		---	---	24	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Notes:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. $V_{DD}=50V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=65A, R_G=25\Omega, \text{Starting } T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu\text{S}$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

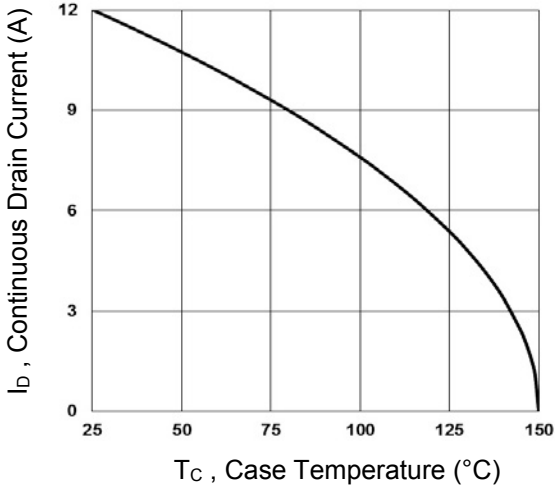


Fig.1 Continuous Drain Current vs. T_c

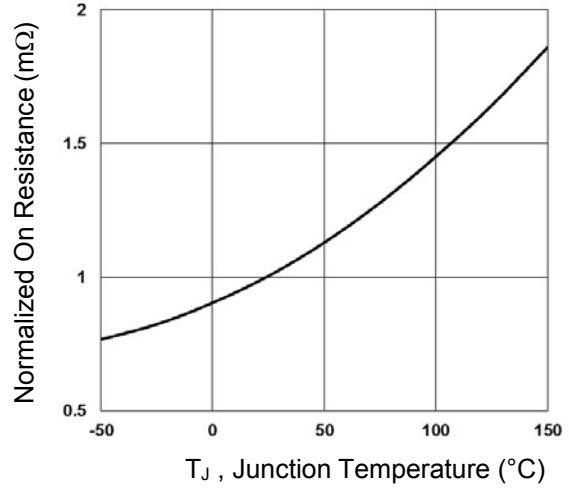


Fig.2 Normalized $R_{DS(ON)}$ vs. T_j

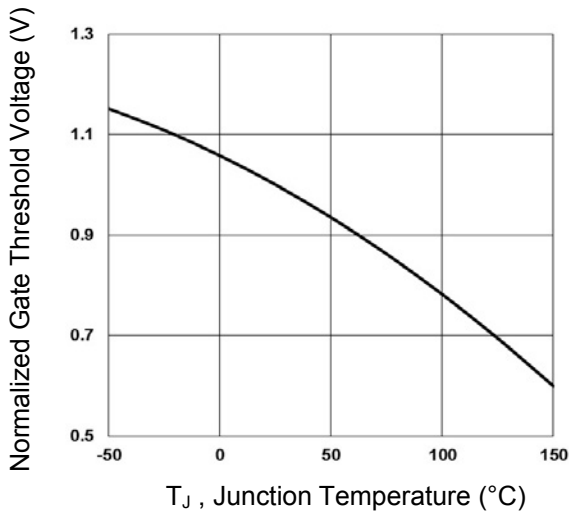


Fig.3 Normalized V_{th} vs. T_j

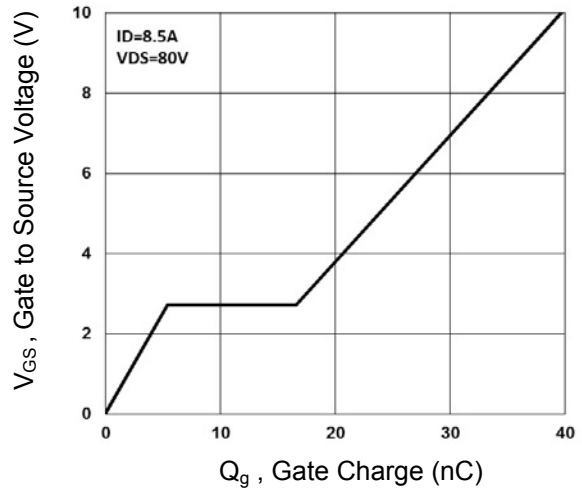


Fig.4 Gate Charge Characteristics

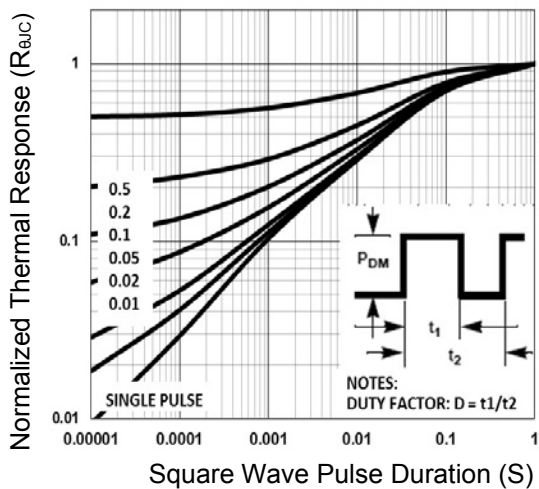


Fig.5 Normalized Transient Impedance

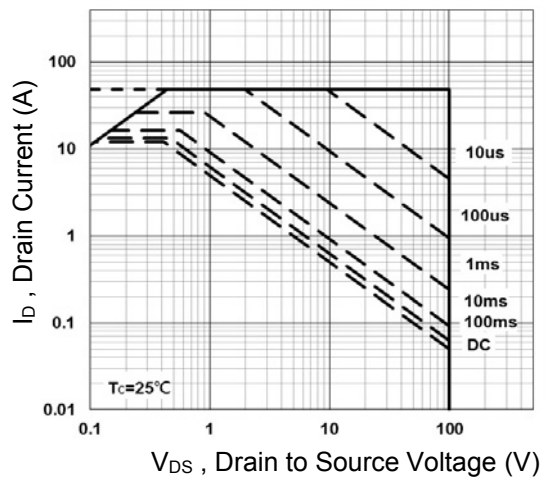


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

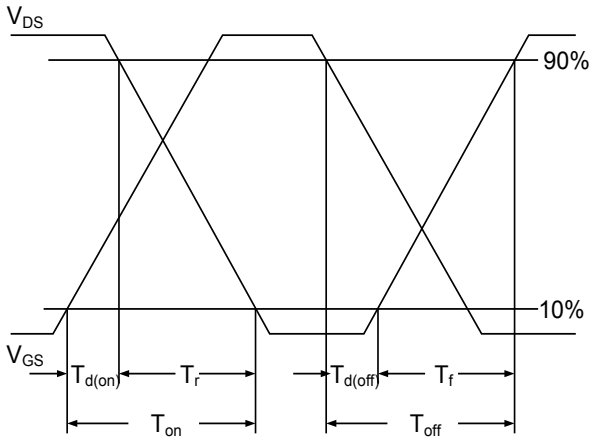


Fig.7 Switching Time Waveform

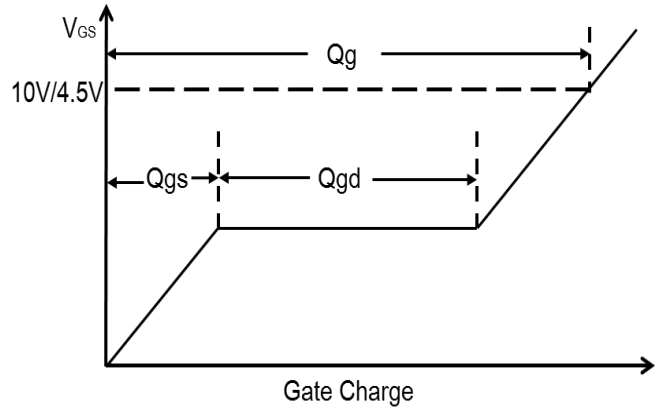
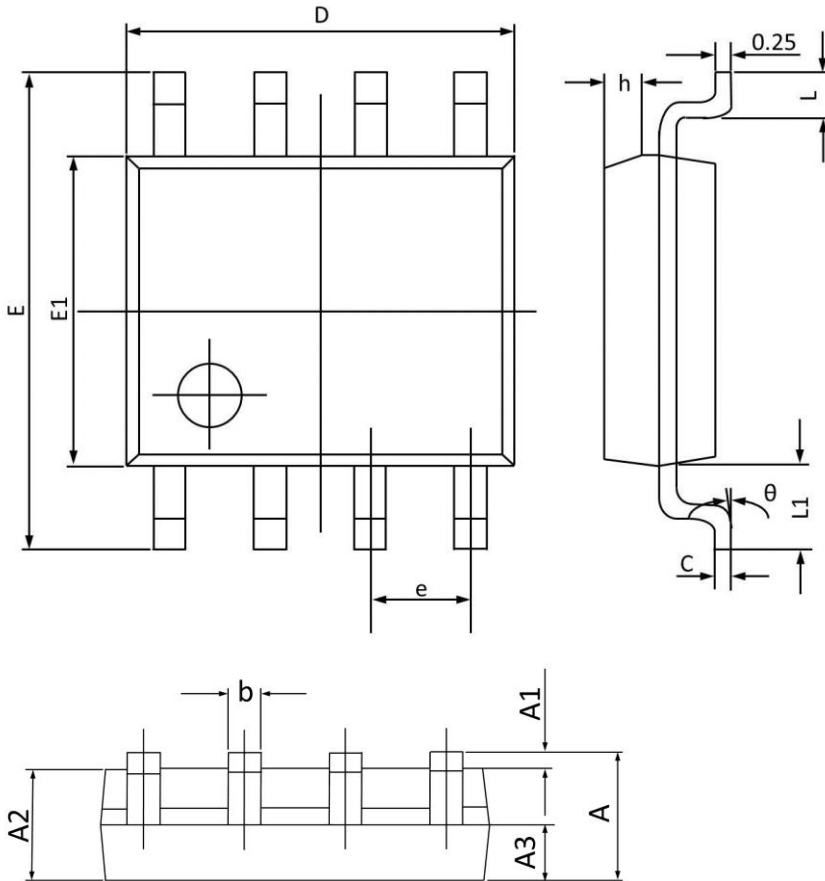


Fig.8 Gate Charge Waveform

Package Outline Dimensions

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050(BSC)		0.041(BSC)	
θ	0°	8°	0°	8°